

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	0	eutectic and "anisotropic conductive film" and "indium tin oxide" and plat\$3 and plug	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 10:57
S1	7	(glass near4 substrate) and interconnect and wafer and chip\$2 and active and bump\$2 and (flip or turn) and dic\$4 and drill\$4 and hol\$2 and via and plug and scale and package	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 08:40
S2	0	(glass near4 substrate) and interconnect and wafer and chip\$2 and active and bump\$2 and (flip or turn) and dic\$4 and drill\$4 and hol\$2 and via and plug and scale and package and "indium tin oxide" and eutectic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 13:50
S3	4	(glass near4 substrate) and interconnect and wafer and chip\$2 and active and bump\$2 and (flip or turn) and dic\$4 and drill\$4 and hol\$2 and via and plug and scale and package and "indium tin oxide"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 13:50
S4	0	(glass near4 substrate) and interconnect and wafer and chip\$2 and active and bump\$2 and (flip or turn) and dic\$4 and drill\$4 and hol\$2 and via and plug and scale and package and "indium tin oxide" and ACF	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 13:50
S5	4	(glass near4 substrate) and interconnect and wafer and chip\$2 and active and bump\$2 and (flip or turn) and dic\$4 and drill\$4 and hol\$2 and via and plug and scale and package and "indium tin oxide"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 10:48
S6	0	"glass substrate" near8 interconnect and (bump or ball) and chips and wafer and dic\$4 and hole and (via near8 plug) and (scale near8 package)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 10:52

S7	0	"glass substrate" near8 interconnect and (bump or ball) and chips and wafer and dic\$4 and hole and (via near8 plug)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 10:52
S8	58	substrate near8 interconnect and (bump or ball) and chips and wafer and dic\$4 and hole and (via near8 plug)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 10:52
S9	58	(substrate near8 interconnect) and (bump or ball) and chips and wafer and dic\$4 and hole and (via near8 plug)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 10:52
S10	47	(substrate near8 interconnect) and (bump or ball) and chips and wafer and dic\$4 and hole and (via near8 plug) and glass	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 10:52
S11	0	(substrate near8 interconnect) and (bump or ball) and chips and wafer and dic\$4 and hole and (via near8 plug) and glass and drill	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 10:53
S12	0	(substrate near8 interconnect) and (bump or ball) and chips and wafer and dic\$4 and hole and (via near8 plug) and glass and scribe	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 10:53
S13	47	(substrate near8 interconnect) and (bump or ball) and chips and wafer and dic\$4 and hole and (via near8 plug) and glass	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 11:06
S14	0	(substrate near8 interconnect) and (bump or ball) and chips and wafer and dic\$4 and hole and (via near8 plug) and glass and "indium tin oxide"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 10:55

S15	6	(substrate near8 interconnect) and (bump or ball) and chips and wafer and dic\$4 and hole and (via near8 plug) and glass and eutectic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 10:57
S16	0	(substrate near8 interconnect) and (bump or ball) and chips and wafer and dic\$4 and hole and (via near8 plug) and glass and eutectic and ACF	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 10:56
S17	0	(substrate near8 interconnect) and (bump or ball) and chips and wafer and dic\$4 and hole and (via near8 plug) and glass and eutectic and anisotropic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 10:57
S18	0	(drill near8 substrate) and interconnect and wafer and chips and bumps and dic\$4 and holes and (via near4 plug)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 11:08
S19	10915	drill and substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 11:50
S20	16	drill and substrate and interconnect and wafer and chips and bumps and dic\$4 and via and plugs	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 11:52
S21	11	drill and substrate and interconnect and wafer and chips and bumps and dic\$4 and via and plugs and (scale near4 package)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 12:00
S22	11	drill and substrate and interconnect and wafer and chips and bumps and dic\$4 and via and plugs and (scale near4 package) and glass	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 11:53

S23	0	drill and substrate and interconnect and wafer and chips and bumps and dic\$4 and via and plugs and (scale near4 package) and glass and "indium tin oxide"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 11:53
S24	0	drill and substrate and interconnect and wafer and chips and bumps and dic\$4 and via and plugs and (scale near4 package) and glass and scribe	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 11:54
S25	0	drill and substrate and interconnect and wafer and cover and chips and scribe and pads and dic\$4 and (via near4 plugs) and (scale near4 package) and glass	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 11:56
S26	6	drill and substrate and interconnect and wafer and chips and bumps and dic\$4 and via and plugs and (scale near4 package) and scrib\$4 and pads	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 12:55
S27	3	drill and substrate and interconnect and wafer and chips and bumps and dic\$4 and via and plugs and (scale near4 package) and scrib\$4 and pads .clm.	US-PGPUB	OR	ON	2005/09/15 13:18
S28	0	drill and substrate and interconnect and wafer and chips and bumps and dic\$4 and via and plugs and (scale near4 package) and scrib\$4 and pads and (438/106.ccls.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 13:20
S29	1	drill and substrate and interconnect and wafer and chips and bumps and dic\$4 and via and plugs and (scale near4 package) and scrib\$4 and pads and (438/108.ccls.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 13:20
S30	3	drill and substrate and interconnect and wafer and chips and bumps and dic\$4 and via and plugs and (scale near4 package) and scrib\$4 and pads and (438/113.ccls.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/30 12:57

S31	9	"6908784"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/30 12:58
S32	0	"CSP" and eutectic and "ACF" and plat\$3 and plug\$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 08:42
S33	0	eutectic and "ACF" and plat\$3 and plug\$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 08:42
S34	1482	eutectic and anisotropic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 08:42
S35	190	eutectic and "anisotropic conductive film"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 08:42
S36	11	eutectic and "anisotropic conductive film" and "indium tin oxide"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 08:43
S37	11	eutectic and "anisotropic conductive film" and "indium tin oxide" and plat\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 10:57